

# KBL4A THRU KBL4M

## SINGLE-PHASE SILICON BRIDGE RECTIFIER

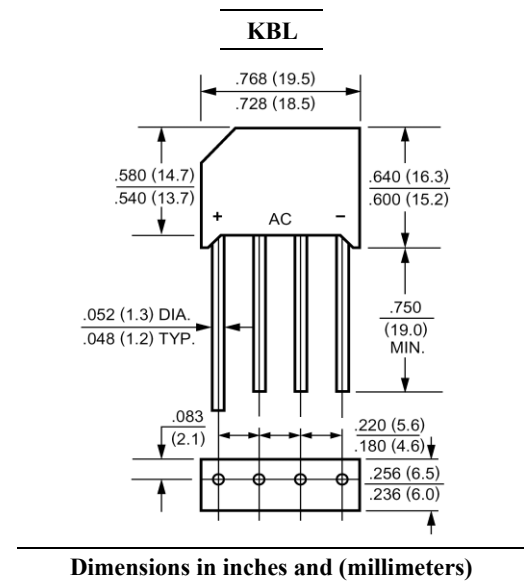
**REVERSE VOLTAGE:** 50 to 1000 VOLTS  
**FORWARD CURRENT:** 4.0 AMPERE

### FEATURES

- Reliable low cost construction utilizing molded plastic technique
- Ideal for printed circuit board
- Low forward voltage drop
- Low reverse leakage current
- High surge current capability

### MECHANICAL DATA

Case: Molded plastic, KBL  
 Epoxy: UL 94V-O rate flame retardant  
 Terminals: Leads solderable per MIL-STD-202, method 208 guaranteed  
 Mounting position: Any  
 Weight: 0.2ounce, 5.6gram



### Maximum Ratings and Electrical Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.  
 Single phase, half wave, 60Hz, resistive or inductive load.  
 For capacitive load, derate current by 20%.

|   | Symbols         | KBL4A       | KBL4B | KBL4D | KBL4G | KBL4J | KBL4K | KBL4M | Units |
|---|-----------------|-------------|-------|-------|-------|-------|-------|-------|-------|
| Maximum Recurrent Peak Reverse Voltage  | $V_{RRM}$       | 50          | 100   | 200   | 400   | 600   | 800   | 1000  | Volts |
| Maximum RMS Voltage   | $V_{RMS}$       | 35          | 70    | 140   | 280   | 420   | 560   | 700   | Volts |
| Maximum DC Blocking Voltage   | $V_{DC}$        | 50          | 100   | 200   | 400   | 600   | 800   | 1000  | Volts |
| Maximum Average Forward Rectified Current<br>.375" (9.5mm) Lead Length at $T_A=50$                      | $I_{(AV)}$      | 4.0         |       |       |       |       |       |       | Amp   |
| Peak Forward Surge Current,<br>8.3ms single half-sine-wave<br>superimposed on rated load (JEDEC method) | $I_{FSM}$       | 200         |       |       |       |       |       |       | Amp   |
| Maximum Forward Voltage<br>at 4.0A DC and 25  | $V_F$           | 1.1         |       |       |       |       |       |       | Volts |
| Maximum Reverse Current at $T_A=25$<br>at Rated DC Blocking Voltage $T_A=100$                           | $I_R$           | 10.0<br>500 |       |       |       |       |       |       | uAmp  |
| Typical Junction Capacitance (Note 1)   | $C_J$           | 40          |       |       |       |       |       |       | pF    |
| Typical Thermal Resistance (Note 2)   | $R_{\theta JA}$ | 19          |       |       |       |       |       |       | /W    |
| Typical Thermal Resistance (Note 3)   | $R_{\theta JL}$ | 2.4         |       |       |       |       |       |       | /W    |
| Operating and Storage Temperature Range   | $T_J, T_{stg}$  | -55 to +125 |       |       |       |       |       |       |       |

### NOTES:

- 1- Measured at 1 MHz and applied reverse voltage of 4.0 VDC.
- 2- Thermal resistance from junction to ambient with units mounted on 3.0 x 3.0 x 0.11" thick (7.5 x 7.5 x 0.3cm) Al. plate
- 3- Thermal resistance from junction to lead with units mounted on P.C.B. at 0.375" (9.5mm) lead length and 0.5 x 0.5" (12 x 12mm) copper pads

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### RATINGS AND CHARACTERISTIC CURVES

FIG.1- MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT PER BRIDGE ELEMENT

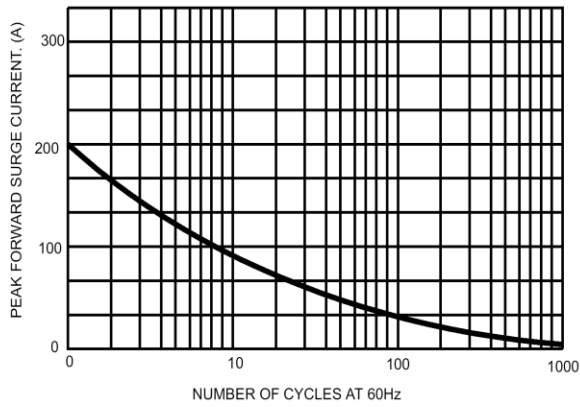


FIG.2- MAXIMUM FORWARD CURRENT DERATING CURVE

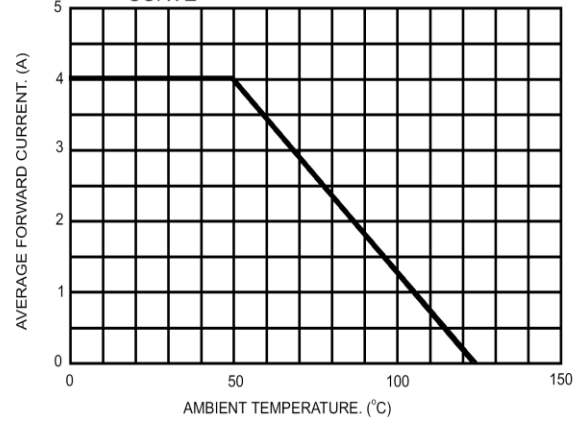


FIG.3- TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS PER BRIDGE ELEMENT

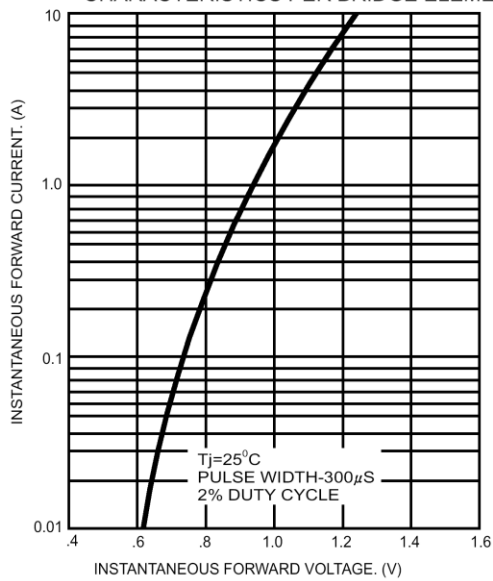


FIG.4- TYPICAL REVERSE CHARACTERISTICS PER BRIDGE ELEMENT

